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Fundamentals of Semiconductor Devices provides a realistic and practical treatment of modern semiconductor devices. A solid understanding of the physical processes responsible for the electronic properties of semiconductor materials and devices is emphasized. With this emphasis, the reader will appreciate the underlying physics behind the equations derived and their range of applicability. The authors clear writing style, comprehensive coverage of the core material, and attention to current topics are key strengths of this book.semiconductor device fundamental.Base Transport Factor Common Base d.c. Current Gain Common Emitter d.c. Current Gain 10.6 Summary Problems Chapter 11 BJT Static Characteristics 11.1 Ideal Transistor Analysis 1.1.1 Solution Strategy Basic Assumptions Notation Diffusion Equations/Boundary Conditions Computational Relationships 11.1.2 General Solution (W Arbitrary) Emitter/Collector Region Solutions Base Region Solution Performance Parameters/Terminal Currents 11.1.3 Simplified Relationships (W < L B) A/? B (x)intheBase Performance Parameters 11.1.4 Ebers-Moll Equations and Model 11.2 Deviations from the Ideal 11.2.1 Ideal Theory/Experiment Comparison 11.2.2 Base Width Modulation 11.2.3 Punch-Through 11.2.4 Avalanche Multiplication and Breakdown Common Base Common Emitter 11.2.5 Geometrical Effects Emitter Area ^ Collector Area Series Resistances Current Crowding2.6 Recombination-Generation Current -^11.2.7 Graded Base 11.2.8 Figures of Merit 11.3 Modern BJT Structures 11.3.1 Poly silicon Emitter BJT 11.3.2 Heterojunction Bipolar Transistor (HBT) Part 1 - Materials1) Electron Energy and States in Semiconductors2)Homogeneous Semiconductors3)Current Flow in Homogeneous Semiconductors4)Nonhomogeneous SemiconductorsSupplement to Part 1Supplement 1ASupplement 1B Part 2 - Diodes5) Prototype pn Homojunctions6)Additional Considerations for DiodesSupplement to Part 2Part 3 - Field-Effect Transistors7) The MOSFET8) Additional Considerations for FETsSupplement to Part 3Part 4 - Bipolar Junction Transistors9) Bipolar Junction Devices: Statics10) Time-Dependent Analysis of BJTsSupplement to Part 4Part 5 - Optoelectronic Devices11) Optoelectronic DevicesAppendix A - ConstantsAppendix B - List of SymbolsAppendix C - FabricationAppendix D - Density-of-States Function, Density-of-States Effective Mass, Conductivity Effective MassAppendix E - Some Useful IntegralsAppendix F - Useful EquationsAppendix G - List of Suggested Readings Help out the community by reporting the quality of this file! 0) A file MD5 is a hash that gets computed from the file contents, and is reasonably unique based on that content. All shadow libraries that we have indexed on here primarily use MD5s to identify files. A file might appear in multiple shadow libraries. For information about the various datasets that we have compiled, see the Datasets page. For information about this particular file, check out its JSON file. Live/debug JSON version. Live/debug page. Image not available forColor: To view this video download Flash Player It looks like you're offline. December 6, 2022 Edited by ImportBot import existing book October 11, 2020 Edited by ImportBot import existing book August 5, 2020 Edited by ImportBot import existing book October 8, 2019 Created by ImportBot Imported fromamazon.com record

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